

FIG. 2 is a cross-sectional view of a device in accordance with the present invention. The device includes a substrate 1, a first layer 2, a second layer 3, a third layer 4, a fourth layer 5, a fifth layer 6, a sixth layer 7, a seventh layer 8, and an eighth layer 9. A channel 10 is formed in the substrate 1, and a plug 11 is formed in the channel 10. A first contact 12 is formed in the first layer 2, and a second contact 13 is formed in the second layer 3. A first electrode 14 is formed in the third layer 4, and a second electrode 15 is formed in the fourth layer 5. A first gate 16 is formed in the fifth layer 6, and a second gate 17 is formed in the sixth layer 7. A first source 18 is formed in the seventh layer 8, and a second source 19 is formed in the eighth layer 9.

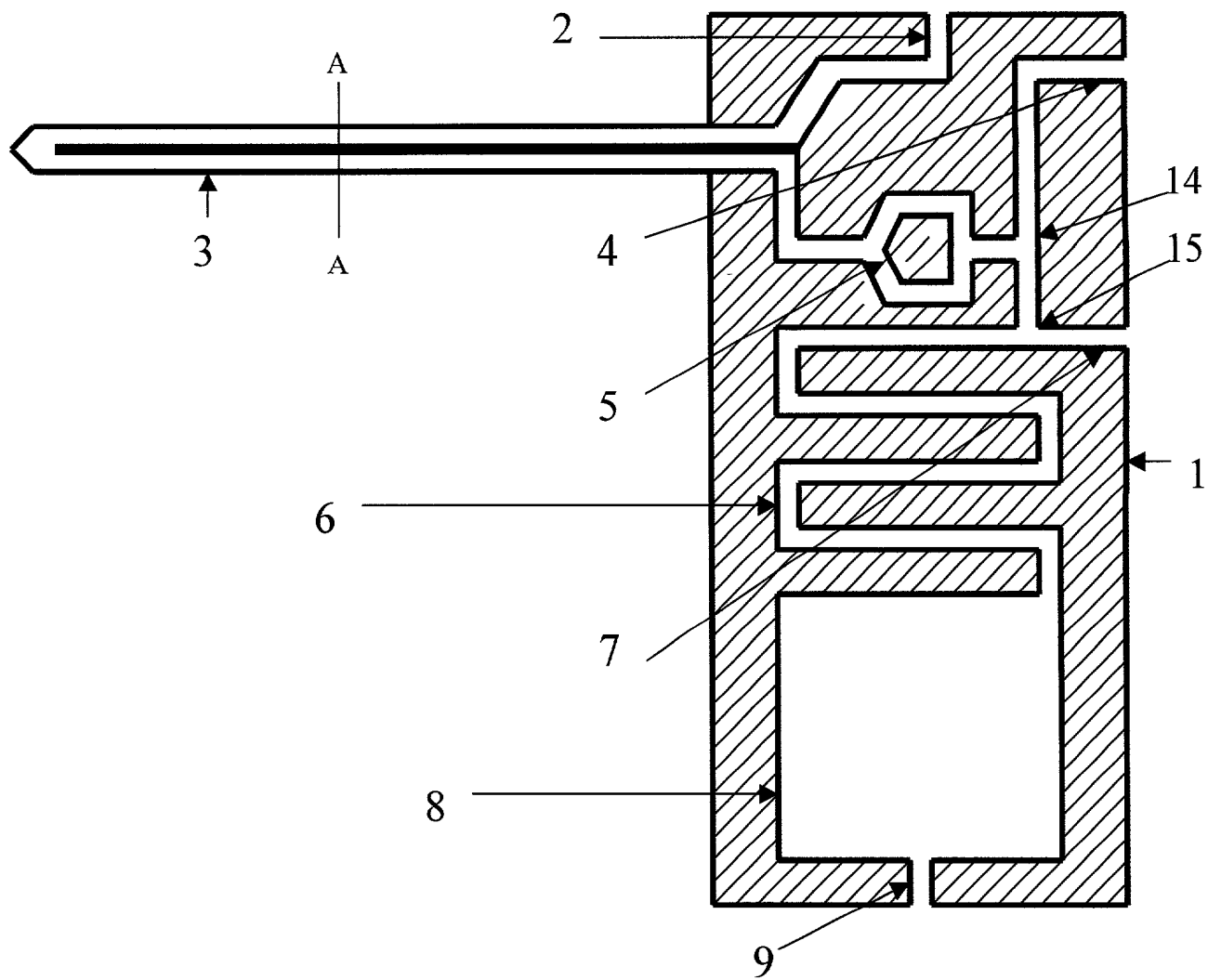


Figure 2

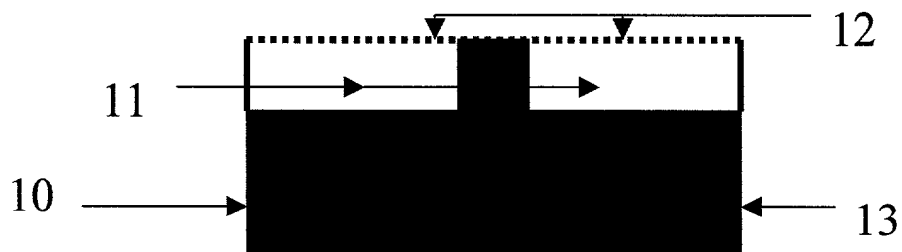


Figure 3

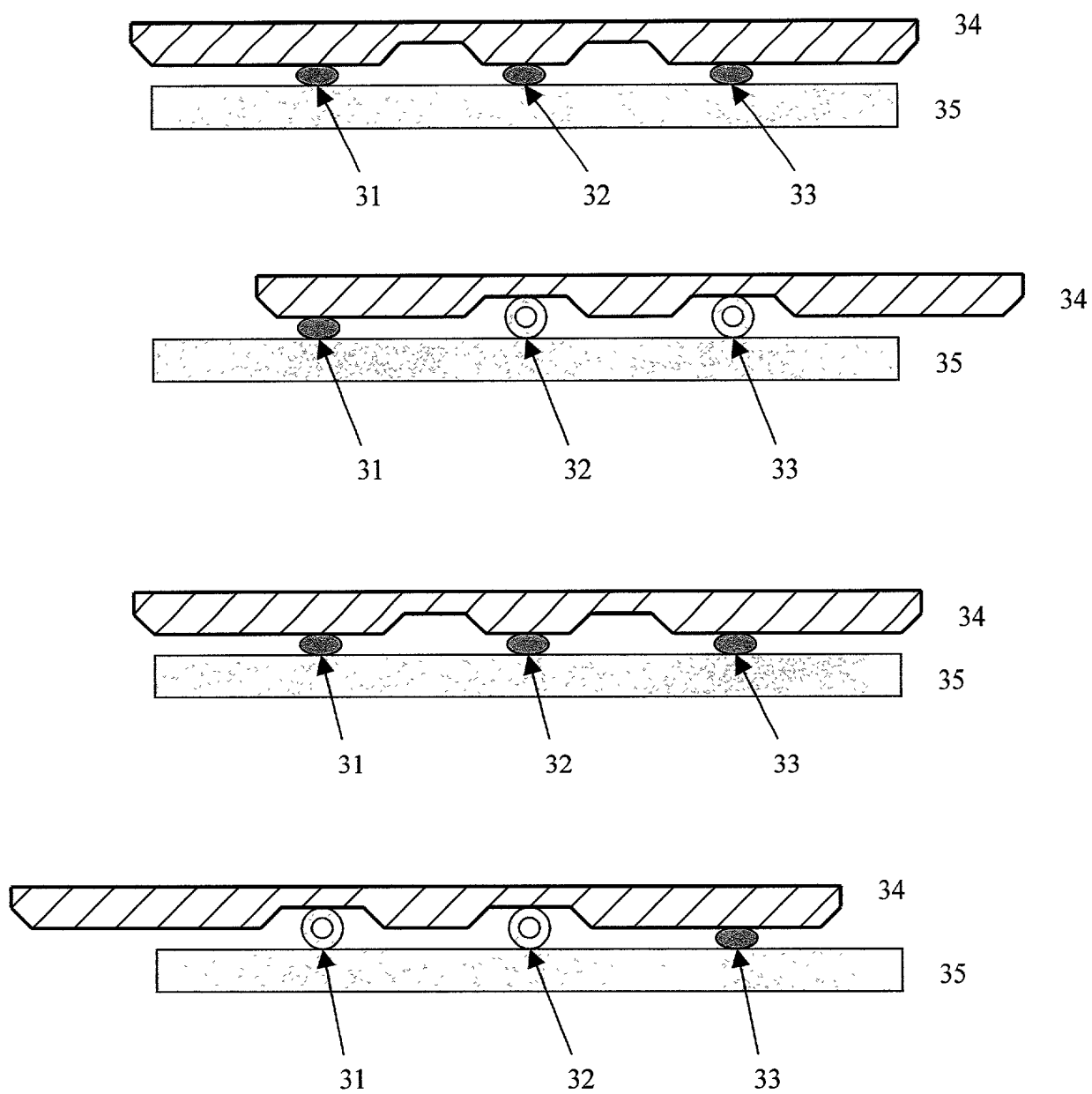


Figure 4